

**PATENT APPLICATION**  
**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of Docket No: Q79703  
Hisayuki MIKI, et al. Allowed: May 19, 2009  
Appln. No.: 10/586,849 Group Art Unit: 2814  
Confirmation No.: 3462 Examiner: Wai Sing LOUIE  
Filed: July 20, 2006

For: GALLIUM NITRIDE-BASED COMPOUND SEMICONDUCTOR MULTILAYER STRUCTURE AND PRODUCTION METHOD THEREOF

**AMENDMENT UNDER 37 C.F.R. §1.312**

**MAIL STOP ISSUE FEE**  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Pursuant to the provisions of 37 C.F.R. §1.312, please amend the above-identified application as follows on the accompanying pages.

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